

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

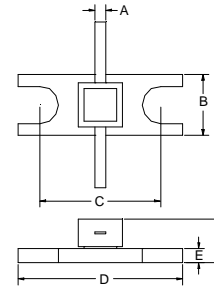
The **ASI OSC-0.3C** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	225 mA
V_{CB}	25 V
P_{DISS}	5.0 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	30 °C/W

PACKAGE STYLE .138 2L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.025 / 0.635	
B	.138 / 3.505	
C	.275 / 6.985	
D	.375 / 9.525	
E	.031 / 0.787	
F	.062 / 1.575	

ORDER CODE: ASI10636
CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 1.0 mA			16			V
BV_{CBO}	I _C = 100 μA			25			V
I_{EBO}	I _{EB} = 1.0 V					2.0	μA
I_{CBO}	V _{CB} = 15 V					500	μA
h_{FE}	V _{CE} = 8.0 V	I _C = 100 mA		20		200	---
C_{OB}	V _{CB} = 10 V	f = 1.0 MHz				1.5	pF
η_C	V _{CC} = 12 V	P _{OUT} = 0.3 W	f = 7.5 GHz		22		%
 S_{21C} ²	V _{CE} = 8.0 V	I _C = 100 mA	f = 1.0 GHz	4.0			dB
P_{OSC}	V _{CC} = 12 V	I _C = 120 mA	f = 7.5 GHz		320		mW